

Monolithic Amplifier PMA2-183LN+

 50Ω 4 to 18 GHz

THE BIG DEAL

- Ultra wideband, 4 to 18 GHz
- Excellent noise figure, 2.5 dB at 15GHz
- Low Current, 48mA
- Usable up to 20 GHz



Generic photo used for illustration purposes only

CASE STYLE: MC1631-1

+RoHS Compliant

The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

APPLICATIONS

- WiFi
- WLAN
- LTE/WCDMA/EDGE
- L, S and C-band Radar
- C-band Satcom

PRODUCT OVERVIEW

The PMA2-183LN+ is a E-PHEMT* based wideband, low noise MMIC amplifier with an unique combination of low noise, high IP3, and low current making it ideal for sensitive, high-dynamic-range receiver applications. This design operates on a single 5V supply, is well matched for 50Ω and comes in a tiny, low profile package (2 x 2 mm, 8 lead MCLP), accommodating dense circuit board layouts.

KEY FEATURES

Feature	Advantages	
Excellent noise figure up to 18 GHz • 2.7 dB typ. at 4 GHz • 2.5 dB typ. at 18 GHz	Enables lower system noise figure performance.	
High IP3 • +31 dBm at 4 GHz • +29.2 dBm at 20 GHz	Combination of low noise figure and high IP3 makes this MMIC amplifier ideal for use in low noise receiver front end (RFE) as it gives the user advantages of sensitivity and two-tone IM performance at both ends of the dynamic range.	
Low operating voltage & current 5V & 48mA	Low voltage & current consumption is ideal for use in amplifier chain.	
2 x 2mm 8-lead MCLP package	Tiny footprint saves space in dense layouts while providing low inductance, repeatable transitions, and excellent thermal contact to the PCB.	

^{*}Enhancement mode Pseudomorphic High Electron Mobility Transistor



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ELECTRICAL SPECIFICATIONS¹ AT 25°C, UNLESS NOTED OTHERWISE

		V _{DD} =5.0			
Parameter	Condition (GHz)	Min.	Тур.	Max.	Units
Frequency Range		4		18	GHz
. 4	4	11.9	13.2	14.5	
	10	10.6	11.8	13.0	
	12	9.4	10.4	11.5	
Gain	15	9.8	10.9	12.0	dB
	18	9.1	10.2	11.2	
	20		9.3		
	4		10		
	10		11		
	12		11		
Input Return Loss	15		15		dB
	18		12		
	20		11		
	4		12		
	10		15		
	12		15		
Output Return Loss	15		20		dB
	18		13		
	20		11		
	4		16		
	10		14.4		
	12		14.2		dBm
Output Power at 1dB Compression	15		15.8		
	18		14.6		
	20		12.8		
	4		31		
	10		26.3		
	12		25.6		dBm
Output IP3	15		28.1		
	18		27.7		
	20		29.2		
	4		2.7		
	10		2.5		
	12		2.5		
Noise Figure	15		2.5		dB
	18		2.5		
	20		2.9		
Device Operating Voltage (V _{DD})		4.75	5	5.25	V
Device Operating Current (I _{DD})		_	48.2	58	mA
Device Current Variation vs. Temperature ²			2.31		μΑ/°C
Device Current Variation vs. Voltage			0.01		mA/mV
Thermal Resistance, junction-to-ground lead			71.9		°C/W

^{1.} Measured on Mini-Circuits Characterization Test Board TB-PMA2-183LN+. See Characterization Test Circuit (Fig. 1)

MAXIMUM RATINGS⁴

Parameter	Ratings	
Operating Temperature (ground lead)	-40°C to 85°C	
Storage Temperature	-65°C to 150°C	
Junction Temperature	141°C	
Total Power Dissipation	0.95W	
Input Power (CW), Vd=5V	+24 dBm (5 minutes max.) +12 dBm (continuous)	
DC Voltage at Pad 5	7V	

^{4.}Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

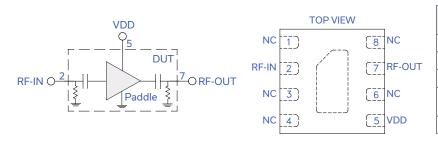


^{2.} Device Current Variation vs. Temperature= (Current at 85°C - Current at -45°C)/130
3. Device Current Variation vs. Voltage = (Current at 5.25V - Current at 4.75V) / ((5.25V-4.75V)*1000 mV/V)



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SIMPLIFIED SCHEMATIC & PAD DESCRIPTION



Function	Pad Number	Description (See Figure 1)
RF-IN	2	Connects to RF input
RF-OUT	7	Connects to RF output
Ground	Paddle	Connects to ground
No Connection	1,3,4,6,8	Not used internally. Connected to ground on Test Board.
V_{DD}	5	Connects to voltage supply

CHARACTERIZATION TEST CIRCUIT

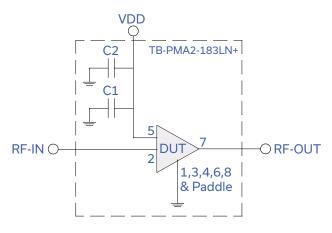


Fig 1. Application and Characterization Circuit

Note: This block diagram is used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-PMA2-183LN+)

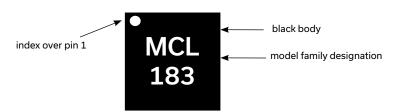
Gain, Return loss, Output power at 1dB compression (P1 dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions

- 1. Gain and Return loss: Pin= -25dBm
- 2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, 0dBm/tone at output.

Component	Size	Value	Part Number	Manufacturer
C1	0402	100 pF	GRM1555C1H101JA01J	Murata
C2	0402	0.1 uF	GRM155R71C104KA88D	Murata

PRODUCT MARKING



Marking may contain other features or characters for internal lot control



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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASH BOARD. TO ACCESS

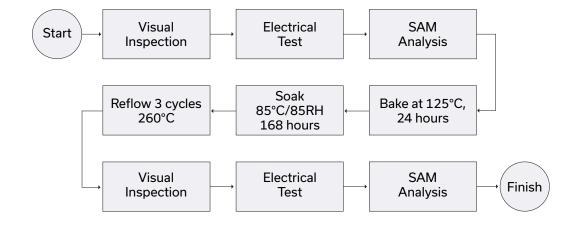
CLICK HERE

	Data Table	
Performance Data	Swept Graphs	
	S-Parameter (S2P Files) Data Set (.zip file)	
Case Style	MC1631-1 Plastic package, exposed paddle, lead finish: Matte-Tin	
Tape & Reel	F66	
Standard quantities available on reel	7" reels with 20, 50, 100, 200, 500,1K or 2K devices	
Suggested Layout for PCB Design	PL-636	
Evaluation Board	TB-PMA2-183LN+	
Environmental Ratings	ENV08T1	

ESD RATING

Human Body Model (HBM): Class 1A (250 to <500V) in accordance with ANSI/ESD STM 5.1 - 2001

MSL TEST FLOW CHART



NOTES

A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.

B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.

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